Technical Data
DIODE

DISCRETE SEMICONDUCTOR INDUSTRIES

maximum ratings

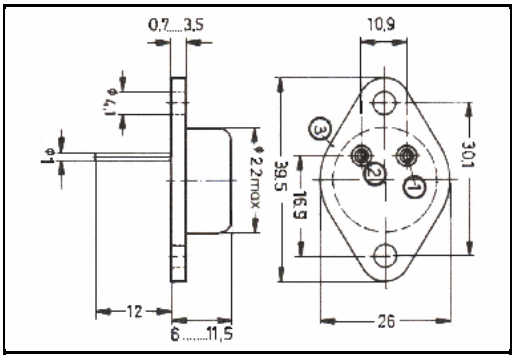
Voltage, Reverse (VZ)	13.0	V	NO.	1N2811B
Voltage, Reverse Peak (VRM)		V	TYPE	50W-ZENER
Current at VR = OV (IO)		A		
Current Average Rectified (IF)		A		
Current Surge Peak (IZM)	3.3	A	CASE	TO-3
Current, Surge (IFM) at tp =		A		ANODE TO CASE
Max. Power Dissipation (PT) at TC = 75 °C	50.0	W		
Max. Thermal Resistance (Rth J-C)	2.0	°C/W		
Max. Junction Temperature (TJ)	175.0	°C		

PERFORMANCE CHARACTERISTICS at T_C = 25°C, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	VF	IF = 10.0 A (1)	-	1.5	V
2.	VZ	IZ = 960.0 mA, tp = 100.0 µs, dc = 0.1%	12.35	13.65	V
3.	IR	VR = 9.9 V	-	5.0	µA
4.	RZ	IZ = 960.0 mA, Δ IZ = 10.0% IZ, f = 1.0 kHZ	-	1.1	Ω
5.	RZ	IZ = 5.0 mA	-	80.0	Ω
6.					
7.					
8.					
9.					
10.					
11.					
12.					
13.					
14.					
15.					
16.					
17.					
18.	-	1 = CATHODE	0.0	0.0	-
19.	-	2 = CATHODE	0.0	0.0	-
20.	-	3 = ANODE	0.0	0.0	-

Notes (1)pulse-tested tp ≤ 300 µs, duty cycle ≤ 2 %

DIMENSIONS in mm



Marking 1N2811B

Customer GENERAL PURPOSE